MBR 1100

SCHOTTKY DIE SPECIFICATION

TYPE: MBR1100

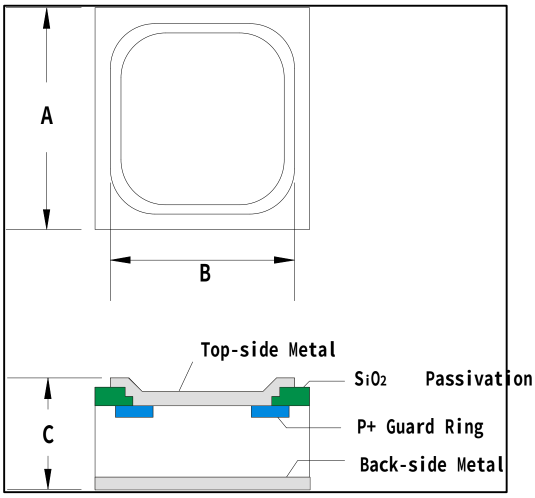
General Description: 100 V 1 A (Low Ir)

(☑Single ☐Dual) Anode

ELECTRICAL CHARACTERISTICS	SYM	Spec. Limit	Die Sort	UNIT
DC Blocking Voltage: Ir=1mA(for wafer form)	VRRM	100	107	Volt
Ir=0.5mA (for dice form)				
Average Rectified Forward Current	IFAV	1		Amp
Maximum Instantaneous Forward Voltage				
@ 1 Amperes, Ta=25℃	VF MAX	0.755	0.725	Volt
Maximum Instantaneous Reverse Voltage				
VR= 103 Volt, Ta=25℃	IR MAX	0.015	0.010	mA
Maximum Junction Capacitance @ 0V, 1MHZ	Cj MAX			pF
MAXIMUM RATINGS				
Nonrepetitive Peak Surge Current	IFSM	52		Amp
Operating Junction Temperature	Tj	-50 to +150		℃
Storage Temperatures	TSTG	-50 to +150		℃

Specification apply to die only. Actual performance may degrade when assembled.
We do not guarantee device performance after assembly.
Data sheet information is subjected to change without notice.

DICE OUTLINE DRAWING



DIM	ITEM	μ m	Mil
A	Die Size	1040	40.94
B	Top Metal Pad Size	880	34.64
C	Thickness (Min)	203	8.00
	Thickness (Max)	254	10.00

PS:

(1)Cutting street width is around 16μ m (0.62mil).

(2)Both of top-side and back-side metals are Ti/Ni/Ag.